

ABSTRACT

Disclosed are a row decoder in a flash memory and erasing method in a flash memory cell using the same. The row decoder comprises a PMOS transistor having a gate electrode for receiving a first input signal as an input and connected between a first power supply terminal and a first node, a first NMOS transistor having a gate electrode for receiving the first input signal as an input and connected between the first node and a second node, a second NMOS transistor having a gate electrode for receiving the second input signal as an input and connected between the second node and a ground terminal, and a switching means having a gate electrode for receiving the third input signal as an input and connected between the second node and a second power supply terminal, wherein the first node is connected to word lines. Therefore, ~~the present invention can prevent an insulating break phenomenon of the ONO insulating film that may happen during an erasing operation such as cycling,~~

etc. *deleted.*

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